TOSHIBA Photocoupler IRED + Photo IC

TLP705F

Plasma Display Panel Industrial Inverter IGBT/Power MOS FET Gate Drive

TLP705F consists of an infrared LED and an integrated photodetector. This unit is 6-lead SDIP package. TLP705F is 50% smaller than 8pin DIP and has suited the safety standard reinforced insulation class. So mounting area in safety standard required equipment can be reduced. TLP705F is suitable for gate driving circuit of IGBT or power MOS FET. Especially TLP705F is capable of "direct" gate drive of lower Power IGBTs.

Peak output current : ±0.45 A (max)
 Operating frequency : 250kHz (max)

Guaranteed performance over temperature : -40 to 100°C

Supply current : 3.0mA (max)
 Power supply voltage : 10 to 20 V

Threshold input current : IFLH = 8 mA (max)

Switching time (tpLH / tpHL)
 Common mode transient immunity
 200 ns (max)
 10 kV/µs (min)

Isolation voltage : 5000 Vrms (min)

· Construction Mechanical Rating

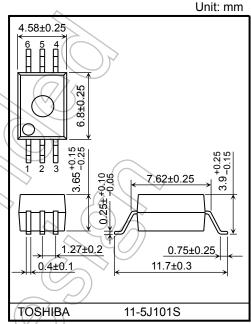
| Creepage Distance | 8.0 mm (min) |
|----------------------|--------------|
| Clearance | 8.0 mm (min) |
| Insulation Thickness | 0.4 mm (min) |

- UL-recognized: UL 1577, File No.E67349
- cUL-recognized : CSA Component Acceptance Service No.5A
 File No.E67349
- VDE-approved : EN 60747-5-5 , EN 62368-1 (Note 1)

Note 1: When a VDE approved type is needed, please designate the **Option(D4)**.

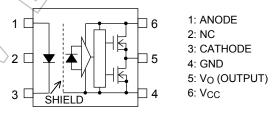
Truth Table

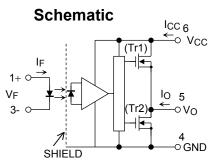
| | | | | 1 |
|-------|-----|-----|-----|--------|
| Input | LED | Tr | Tr2 | Output |
| Н | ON | ON | OFF | Н |
| L | OFF | OFF | ON | L |



Weight: 0.26 g (typ.)

Pin Configuration (Top View)





Note: A 0.1 μF bypass capacitor must be connected between pins 6 and 4.

Start of commercial production 2004-04

Absolute Maximum Ratings (Ta = 25°C)

| | Characteristics | Symbol | Rating | Unit | |
|--|--|----------|----------------------|------------|---------|
| | Forward current | | lF | 20 | mA |
| | Forward current derating (Ta ≥ 85°C) | | ΔΙϝ/ΔΤα | -0.54 | mA/°C |
| | Peak transient forward current | (Note 1) | IFP | 1 | ⟨A |
| LED | Reverse voltage | VR | 5 | V | |
| | Diode power dissipation | | PD | 40 | mW |
| | Diode power dissipation derating (Ta ≥ 85° | C) | ΔP _D /°C | -1.0 | mW/°C |
| | Junction temperature | | Tj | 125 | //°¢\ |
| | "H" peak output current | (Note 2) | Іорн | -0.45 | A |
| | "L" peak output current | (Note 2) | IOPL | 0.45 | A |
| tor | Output voltage | | Vo | 25 | V |
| Detector | Supply voltage | | Vcc | 25 | V |
| | Power dissipation | | Pc | 400 | mW (|
| | Power dissipation derating (Ta ≥25°C) | | ΔP _C / °C | 4.0 | mW / °C |
| | Junction temperature | | Tj | 125 | |
| Oper | rating frequency | (Note 3) | | 250 | kHz |
| Stora | Storage temperature range | | Tstg | -55 to 125 | CC |
| Oper | Operating temperature range | | | -40 to 100 | , e |
| Lead soldering temperature (10 s) (Note 4) | | Tsol | 260 | ∕)°C | |
| Isola | tion voltage (AC, 60 s, R.H. ≤ 60 %) | (Note 5) | BVs | 5000 | Vrms |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note: A ceramic capacitor (0.1 µF) should be connected from pin 6 to pin 4 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property.

The total lead length between capacitor and coupler should not exceed 1 cm.

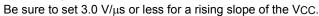
- Note 1: Pulse width $P_W \le 1 \mu s$, 300 pps
- Note 2: Exponential waveform pulse width P_W ≤ 2 μs, f ≤15 kHz
- Note 3: Exponential waveform I_{OPH} ≤-0.25 A (P_W ≤80 ns), I_{OPL} ≤+0.25 A (P_W ≤80 ns), Ta = 100 °C
- Note 4: It is effective soldering area of Lead.
- Note 5: Device considered a two terminal device: pins 1, 2 and 3 shorted together, and pins 4, 5 and 6 shorted together.

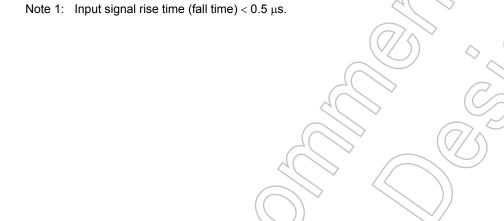
Recommended Operating Conditions

| Characteristics | | Symbol | Min | Тур. | Max | Unit |
|-----------------------|----------|------------------|------|------|--------|------|
| Input current, ON | (Note 1) | IF (ON) | 10 | _ | 15 | mA |
| Input voltage, OFF | | VF (OFF) | 0 | | 0.8 | ٧ |
| Supply voltage | | Vcc | 10 | _ | 20 | V |
| Peak output current | | IOPH / IOPL | _ | _ | ± 0.15 | Α |
| Operating temperature | | T _{opr} | - 40 | | 100 | °C |

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Note: If the rising slope of the supply voltage (VCC) for the detector is steep, stable operation of the internal circuits cannot be guaranteed.





Electrical Characteristics (Ta = -40 to 100°C, unless otherwise specified)

| Characteristic | :S | Symbol | Test Circuit | Test Condition | | Min | Тур. | Max | Unit |
|-----------------------------------|-------------------|----------------------|---|--|---------------------------|-------|------|-----|-------|
| Forward voltage | | VF | _ | I _F = 10 mA, Ta = 25 | °C | _ | 1.6 | 1.8 | V |
| Temperature coefficient o voltage | of forward | ΔV _F /ΔTa | _ | IF = 10 mA | | | -2.0 | _ | mV/°C |
| Input reverse current | | IR | _ | V _R = 5 V, Ta = 25 °C | C | | _ | 10 | μΑ |
| Input capacitance | | Ст | _ | V = 0 V, f = 1 MHz, | Ta = 25 °C | ((-)) | 45 | _ | pF |
| | Vcc = 15 V | | V _{CC} = 15 V | / ₆₋₅ = 4 V | -0.15 | -0.35 | _ | | |
| Output current | "H" Level IOPH | IOPH | 1 | $I_F = 10 \text{ mA}$ | / ₆₋₅ = 10 V | -0.3 | -0.6 | _ | A |
| (Note 1) | "L" Level lopu | la | 2 | V _{CC} = 15 V | / ₅₋₄ = 2 V | 0.15 | 0.36 | _ | |
| | L Levei | IOPL | Z - - - - | | / ₅₋₄ = 10 V | 0.3 | 0.62 | _ | |
| Output voltage | "H" Level | V _{OH} | 3 | | O = -100 mA, F = 10 mA | 6.0 | 8.5 | _ | - v |
| Output voltage | "L" Level | V _{OL} | 4 | | O = 100 mA, F = 0.8 V | | 0.4 | 1.0 | |
| Cumply ourrant | "H" Level | Іссн | 5 | V _{CC} = 10 to 20 V | = 10 mA 🔷 | 5 | 2.0 | 3.0 | m 1 |
| Supply current | "L" Level | ICCL | 6 | Vo = open | F = 0 mA | 4 | 2.0 | 3.0 | mA |
| Threshold input current | $L \rightarrow H$ | I _{FLH} | _ | V _{CC} = 15 V, V _O > 1 V | | | 2.5 | 8 | mA |
| Threshold input voltage | $H \rightarrow L$ | V _{FHL} | _ | V _{CC} = 15 V, V _O < 1 V | | 0.8 | _ | _ | V |
| Supply voltage | | Vcc | ((| <u> </u> | | 10 | _ | 20 | V |

Note: All typical values are at Ta = 25°C

Note: This product is more sensitive than the conventional product to static electricity (ESD) because of a lowest power consumption design.

General precaution to static electricity (ESD) is necessary for handling this component.

Note 1: Duration of IO time \leq 50 μ s

Isolation Characteristics (Ta = 25°C)

| Characteristic | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-----------------------------|--------|------------------------------------|------------------|------------------|-----|------|
| Capacitance input to output | Cs | V = 0 V, f = 1 MHz | _ | 1.0 | _ | pF |
| Isolation resistance | Rs | R.H. ≤ 60 %, V _S = 500V | 10 ¹² | 10 ¹⁴ | _ | Ω |
| Isolation voltage | BVs | AC, 60 s | 5000 | - | _ | Vrms |

Note: Device considered a two terminal device: pins 1, 2 and 3 shorted together, and pins 4, 5 and 6 shorted together.

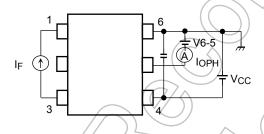
Switching Characteristics (Ta = -40 to 100°C, unless otherwise specified)

| Characteristics | | Symbol | Test Circuit | Test Condition | | Min | Тур. | Max | Unit |
|--|-------------------|-------------------------------------|-------------------------------------|---|---|--------|-------------------------|-----|------|
| Propagation delay time | $L \rightarrow H$ | tpLH | | | Ta = 25 °C I _F = 0→10 mA | 70 | 95 | 170 | |
| | $H \rightarrow L$ | t _{pHL} | | | Ta = 25 °C I _F = 10→ 0 mA | 70 | 105 | 170 | |
| | $L \rightarrow H$ | t _{pLH} | | | Ta = -40 to100 °C I _F = 0→10 mA | 50 | | 200 | |
| Propagation delay time | $H \rightarrow L$ | t _{pHL} | | $V_{CC} = 20 \text{ V}$ $R_g = 30 \Omega$ | Ta = -40 to100 °C I _F = 10→0 mA | 50 | | 200 | |
| Propagation delay skew | (Note 1) | tpsk | 7 | $C_g = 1 \text{ nF}$ F = 250 kHz Duty Cycle = 50 % | Ta= -40 to100 °C I _F = 10 mA | -90 | _ | 90 | ns |
| Switching time dispersion between ON and OFF | | t _{pHL} -t _{pLH} | | | Ta= -40 to100 °C I _F = 10 mA | -65 | / | 65 | |
| Output rise time (10-90%) | 1 | tr | | | I _F = 0 → 10 mA | -\(| | > — | |
| Output fall time (90-10%) | | | $I_F = 10 \rightarrow 0 \text{ mA}$ | | 1 | _ | | | |
| Common mode transient i at high level output | mmunity | СМн | 0 | V _{CM} = 1000 Vp-p | IF = 10 mA VO (min) = 16 V | -10000 | $\widehat{\mathcal{A}}$ | _ | Mus |
| Common mode transient immunity at low level output | | CML | 8 | V _{CC} = 20 V Ta = 25 °C | IF = 0 mA VO (max) = 1 | 10000 | <i>9</i> | _ | V/μs |

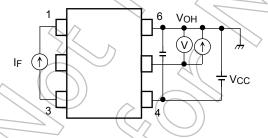
Note: All typical values are at Ta = 25 °C

Note 1: Propagation delay difference between any two parts.

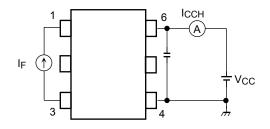




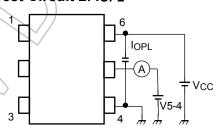
Test Circuit 3: Voн



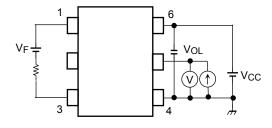
Test Circuit 5: Icch



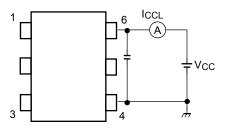
Test Circuit 2: IOPL



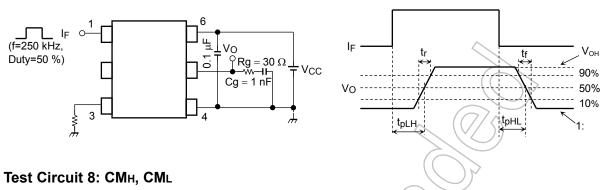
Test Circuit 4: Vol

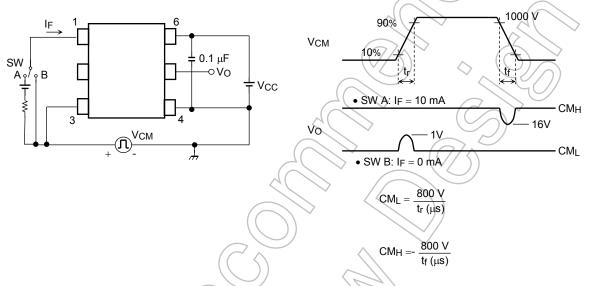


Test Circuit 6: ICCL

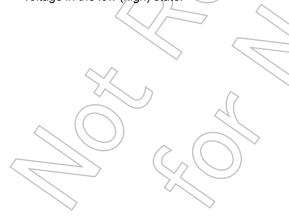


Test Circuit 7: tplн, tpнL, tr, tf, PWD





Note: CML (CMH) is the maximum rate of rise (fall) of the common mode voltage that can be sustained with the output voltage in the low (high) state.



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